

N-Channel Enhancement Mode Power MOSFET

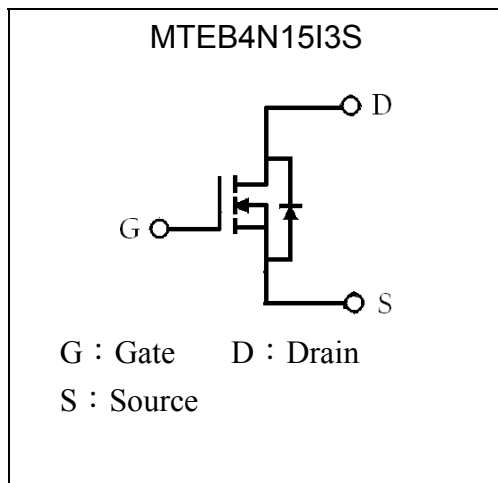
MTEB4N15I3S

BV _{DSS}	150V	
I _D @ V _{GS} =10V, T _c =25°C	6A	
R _{DS(on)} (TYP)	V _{GS} =10V, I _D =3A	253mΩ
	V _{GS} =6V, I _D =2A	265mΩ

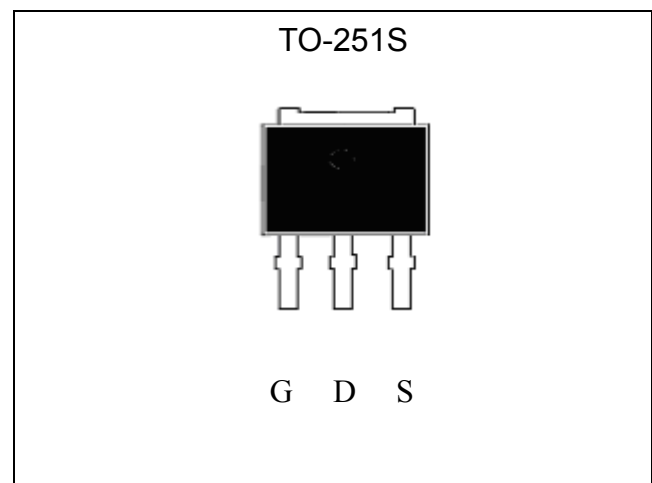
Features

- Low Gate Charge
- Simple Drive Requirement
- Pb-free lead plating and halogen-free package

Equivalent Circuit

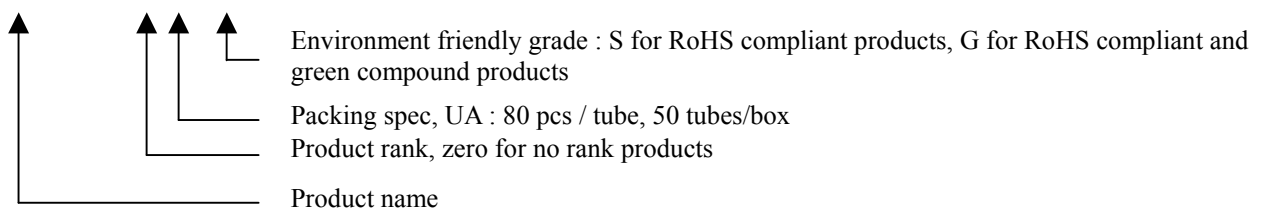


Outline



Ordering Information

Device	Package	Shipping
MTEB4N15I3S-0-UA-G	TO-251S (RoHS compliant and halogen-free package)	80 pcs/tube, 50 tubes/box



**Absolute Maximum Ratings** ($T_C=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current @ $V_{GS}=10\text{V}$, $T_C=25^\circ\text{C}$ (Note 1)	I_D	6	A
Continuous Drain Current @ $V_{GS}=10\text{V}$, $T_C=100^\circ\text{C}$ (Note 1)		4.2	
Continuous Drain Current @ $V_{GS}=10\text{V}$, $T_A=25^\circ\text{C}$ (Note 2)		2	
Continuous Drain Current @ $V_{GS}=10\text{V}$, $T_A=70^\circ\text{C}$ (Note 2)		1.6	
Pulsed Drain Current (Note 3)	I_{DM}	24	
Avalanche Current (Note 3)	I_{AS}	11	mJ
Avalanche Energy @ $L=0.5\text{mH}$, $I_D=4\text{A}$, $V_{DD}=50\text{V}$ (Note 2)	E_{AS}	4	
Repetitive Avalanche Energy @ $L=0.1\text{mH}$ (Note 3)	E_{AR}	2	
Total Power Dissipation @ $T_C=25^\circ\text{C}$ (Note 1)	P_D	25	W
Total Power Dissipation @ $T_C=100^\circ\text{C}$ (Note 1)		12	
Total Power Dissipation @ $T_A=25^\circ\text{C}$ (Note 2)	P_{DSM}	2.5	
Total Power Dissipation @ $T_A=70^\circ\text{C}$ (Note 2)		1.6	
Operating Junction and Storage Temperature Range	T_j, T_{stg}	$-55\sim+175$	$^\circ\text{C}$

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{\theta JC}$	6	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max (Note 2)	$R_{\theta JA}$	50	
Thermal Resistance, Junction-to-ambient, max (Note 4)		110	

- Note : 1. The power dissipation P_D is based on $T_{J(MAX)}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with $T_A=25^\circ\text{C}$. The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=175^\circ\text{C}$. Ratings are based on low frequency and low duty cycles to keep initial $T_J=25^\circ\text{C}$.
4. When mounted on the minimum pad size recommended (PCB mount), $t \leq 10\text{s}$.



Characteristics (Tc=25°C, unless otherwise specified)

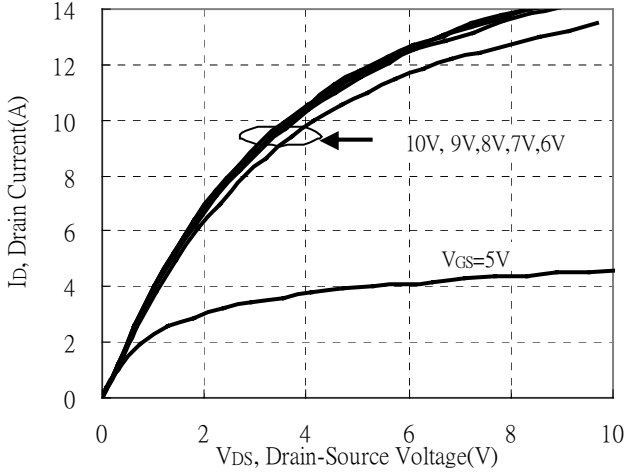
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	150	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	2	-	4		V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	-	-	±100	nA	V _{GS} =±30V, V _{DS} =0V
I _{DSS}	-	-	1	μA	V _{DS} =120V, V _{GS} =0V
	-	-	25		V _{DS} =120V, V _{GS} =0V, T _J =125°C
R _{DS(ON)} *1	-	253	330	mΩ	V _{GS} =10V, I _D =3A
	-	265	345		V _{GS} =6V, I _D =2A
G _{FS} *1	-	3	-	S	V _{DS} =15V, I _D =3A
Dynamic					
Q _g *1, 2	-	7.2	-	nC	V _{DS} =75V, I _D =6A, V _{GS} =10V
Q _{gs} *1, 2	-	1.5	-		
Q _{gd} *1, 2	-	3	-		
t _{d(ON)} *1, 2	-	6	-	ns	V _{DS} =25V, I _D =1A, V _{GS} =10V, R _G =6Ω
t _r *1, 2	-	8	-		
t _{d(OFF)} *1, 2	-	8	-		
t _f *1, 2	-	2	-		
C _{iss}	-	280	-	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
C _{oss}	-	33	-		
C _{rss}	-	12	-		
Source-Drain Diode					
I _S *1	-	-	6	A	
I _{SM} *3	-	-	24		
V _{SD} *1	-	0.78	1.2	V	I _S =2A, V _{GS} =0V
t _{rr}	-	28	-	ns	I _F =2A, dI _F /dt=100A/μs
Q _{rr}	-	36	-	nC	

Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
 *2.Independent of operating temperature
 *3.Pulse width limited by maximum junction temperature.

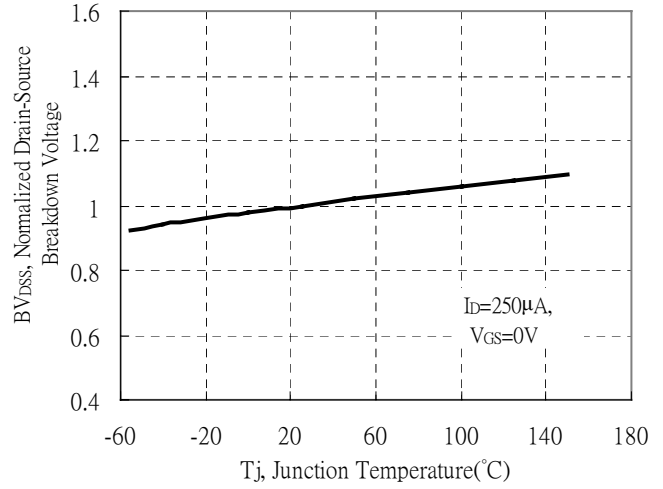


Typical Characteristics

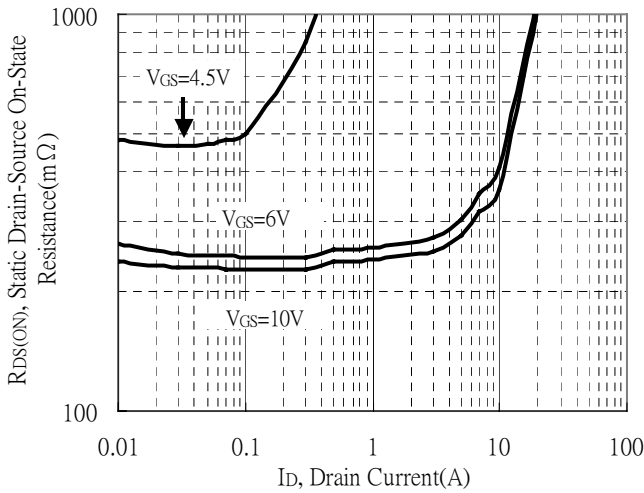
Typical Output Characteristics



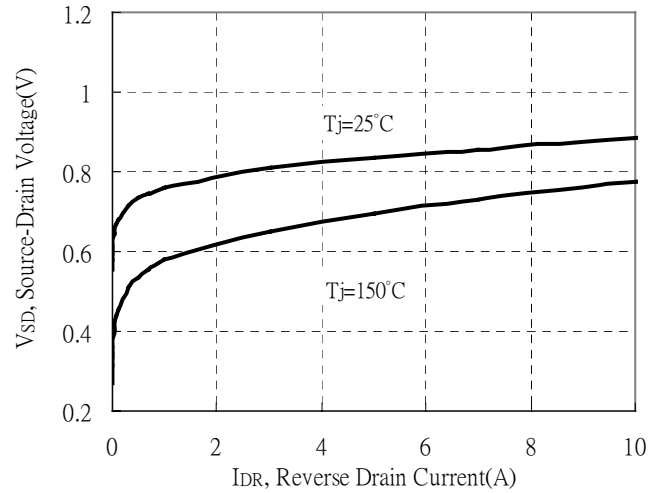
Brekdown Voltage vs Ambient Temperature



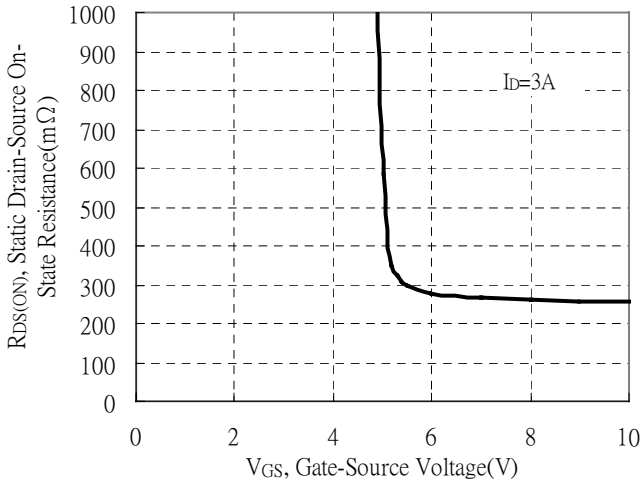
Static Drain-Source On-State resistance vs Drain Current



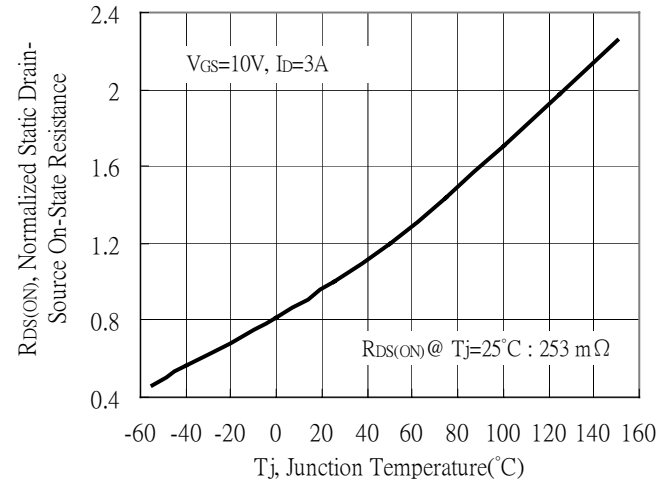
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

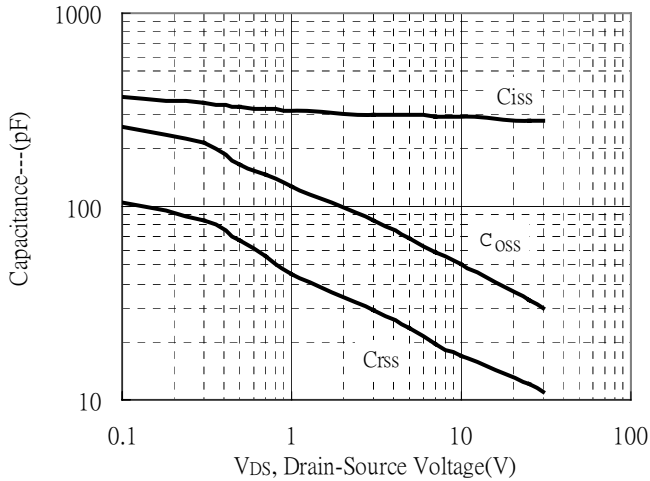


Drain-Source On-State Resistance vs Junction Temperature

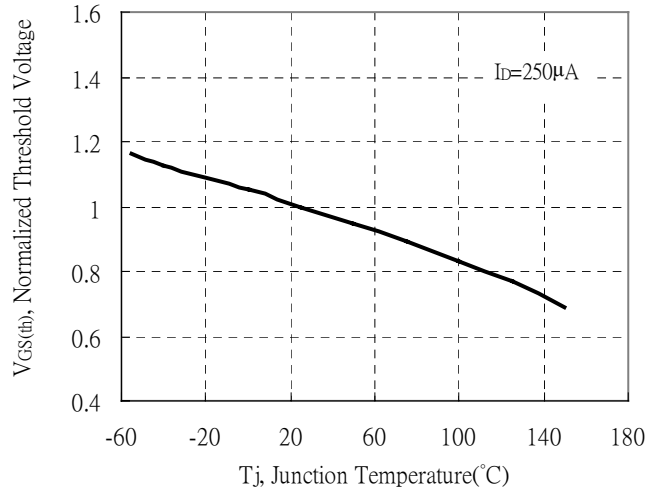


Typical Characteristics(Cont.)

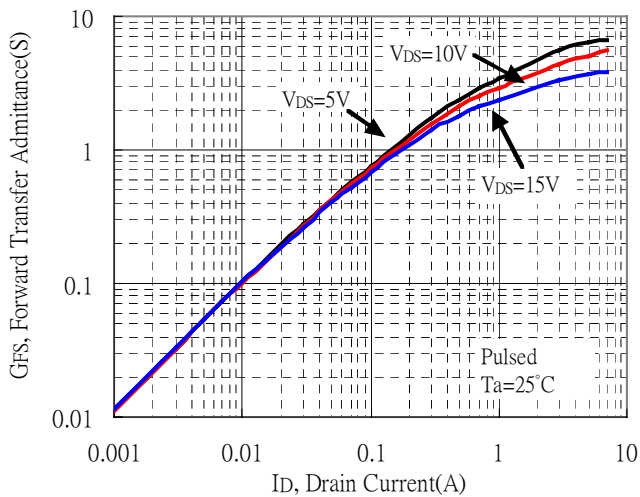
Capacitance vs Drain-to-Source Voltage



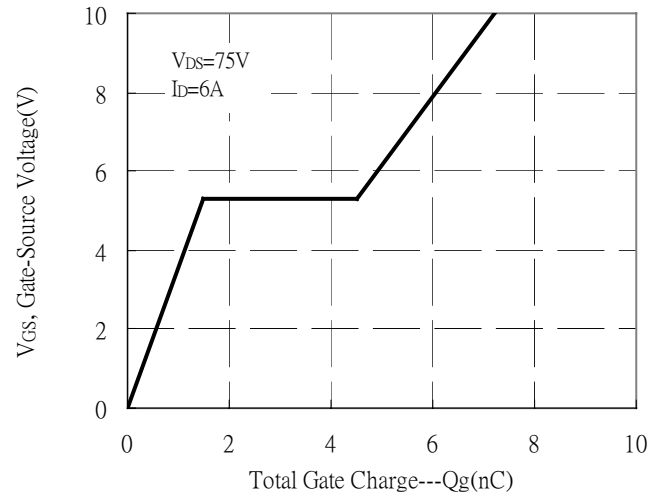
Threshold Voltage vs Junction Temperature



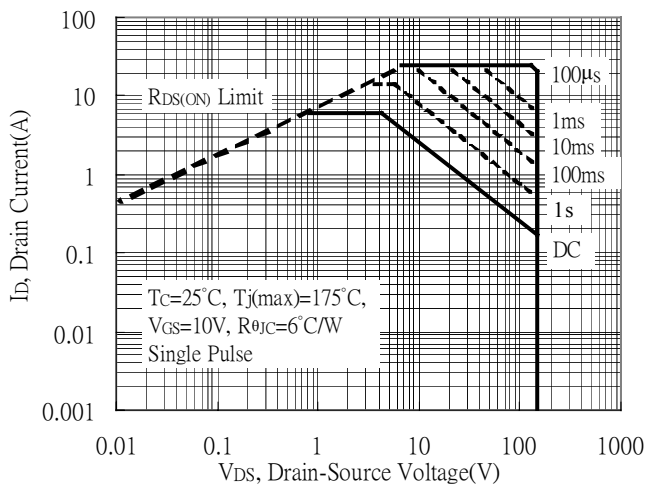
Forward Transfer Admittance vs Drain Current



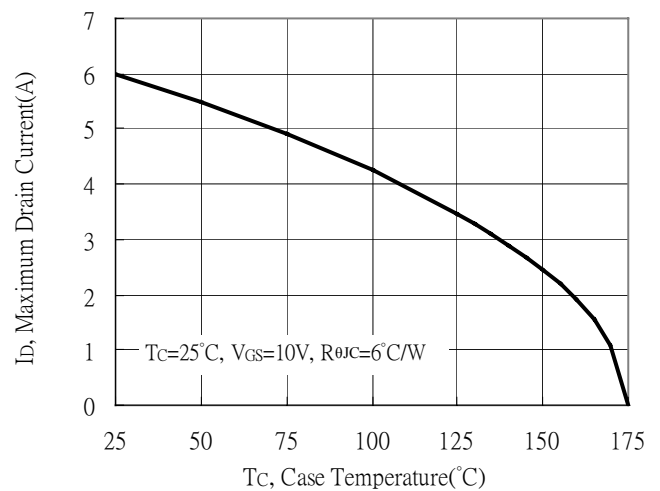
Gate Charge Characteristics



Maximum Safe Operating Area

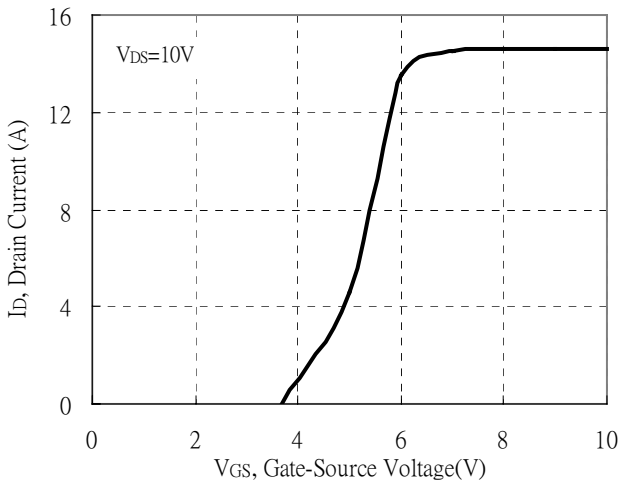


Maximum Drain Current vs Case Temperature

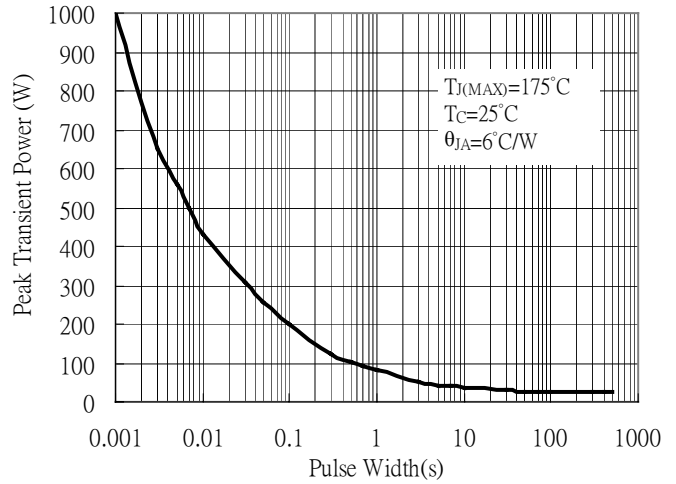


Typical Characteristics(Cont.)

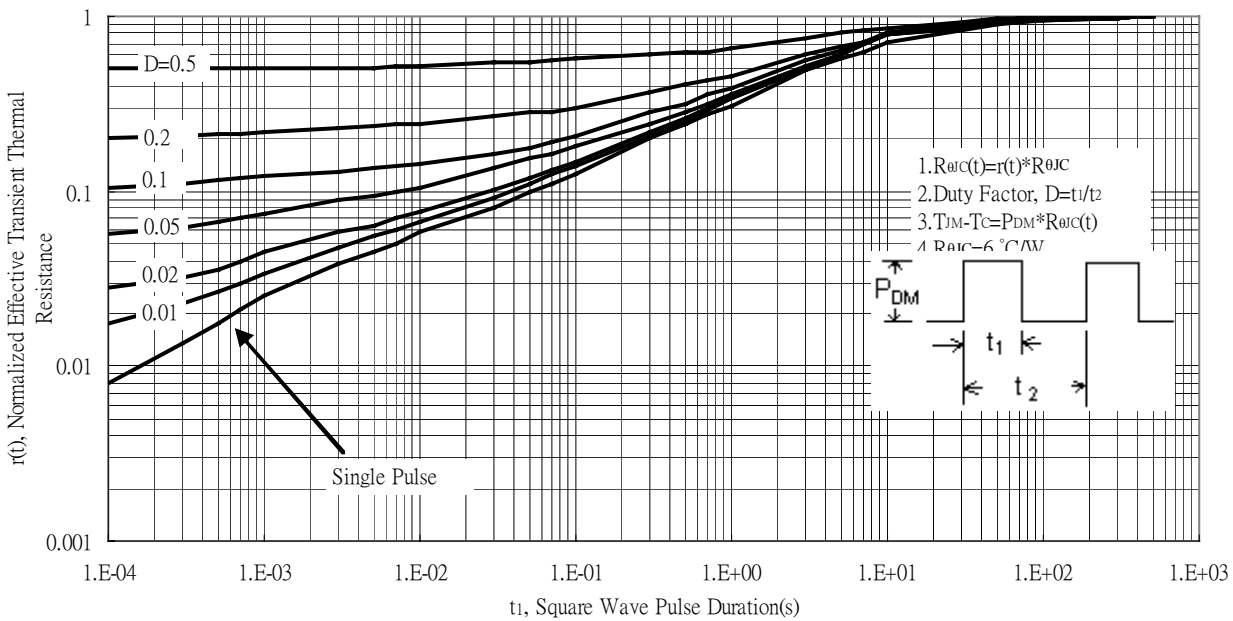
Typical Transfer Characteristics



Single Pulse Maximum Power Dissipation



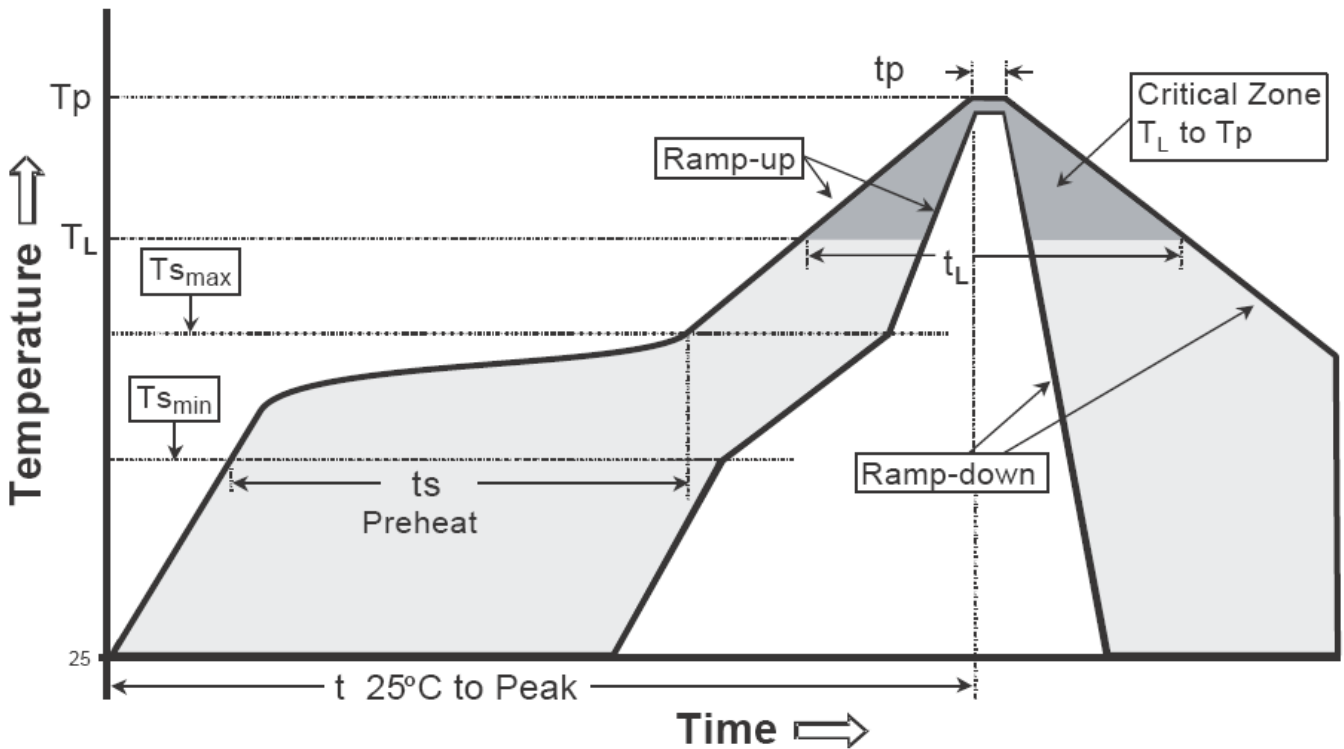
Transient Thermal Response Curves



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

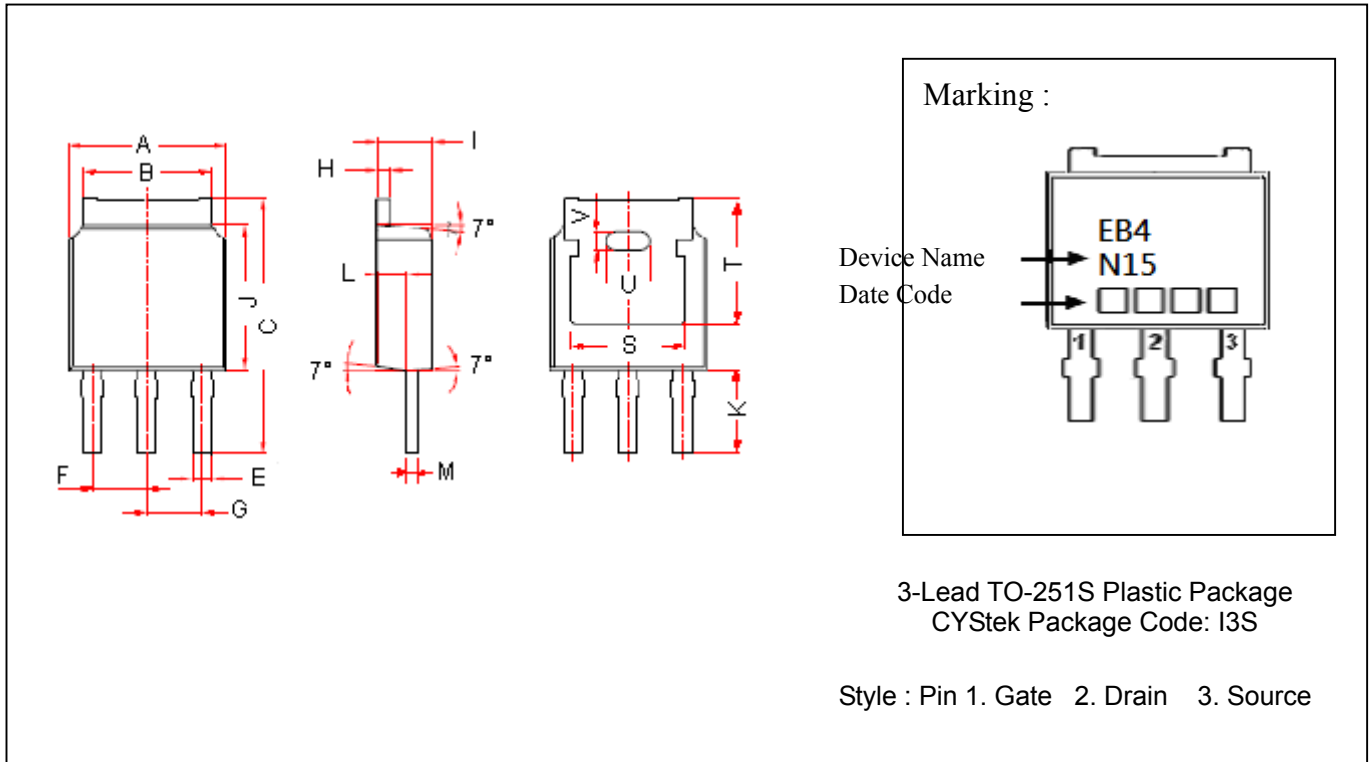
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-251S Dimension



Marking :

Device Name → EB4
 Date Code → N15

3-Lead TO-251S Plastic Package
 CYStek Package Code: I3S

Style : Pin 1. Gate 2. Drain 3. Source

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.2559	0.2638	6.50	6.70	J	0.2362	0.2441	6.00	6.20
B	0.2020	0.2126	5.13	5.46	K	0.1299	0.1457	3.30	3.70
C	0.4094	0.4331	10.40	11.00	L	0.0358	0.0437	0.91	1.11
E	0.0280	0.0319	0.71	0.81	M	0.0181	0.0220	0.46	0.56
F	0.0858	0.0941	2.18	2.39	S	0.1902	REF	4.83	REF
G	0.0858	0.0941	2.18	2.39	T	0.2106	REF	5.35	REF
H	0.0181	0.0220	0.46	0.56	U	0.0701	REF	1.78	REF
I	0.0902	0.0937	2.29	2.38	V	0.0299	REF	0.76	REF

Notes: 1. Controlling dimension: inch.
 2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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